

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	505	438/4.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:06
S2	479	S1 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 11:48
S3	1316	photoresist and critical adj dimension and electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 13:23
S4	113	photoresist same critical adj dimension same electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 13:23
S5	107	S4 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 13:40
S6	6	electron adj beam same reduce near2 feature adj size	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 17:10
S7	810	430/30.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 17:10
S8	699	S7 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 09:13

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S9	230	S8 and electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 17:37
S10	249	S8 and (electron adj beam (e adj beam))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:07
S11	1	@pn="6653231"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:07
S12	1	@pn="6630288"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:09
S13	1	@pn="5468595"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:14
S14	2	"20020160628"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:15
S15	2	"20020160320"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:31
S16	812	430/30.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:31

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S17	701	S16 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:31
S18	230	S17 and electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 09:31
S19	471	S17 not S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 10:20
S20	1	@pn="6340556"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 15:23
S21	3	measur\$3 near2 feature and repair near2 subsequent and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 13:39
S22	19	measur\$3 near2 critical and dimension and photoresist and repair	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 13:40
S23	16	S22 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 13:40
S24	14	measur\$3 near2 critical adj dimension and photoresist and repair	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 13:40

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S25	11	S24 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:06
S26	0	semiconductor adj device adj functionality adj test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 15:23
S27	5	semiconductor adj device near8 functionality adj test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 15:23
S28	154	438/4.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:07
S29	147	S28 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:07
S30	1064	438/14.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:07
S31	147	S29 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:08
S32	981	S30 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 16:08

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S33	3051	photoresist same critical adj dimension	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 16:52
S34	728	S33 and ((electron adj beam) ebeam (e adj beam))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 16:51
S35	166	photoresist same critical adj dimension same ((electron adj beam) ebeam (e adj beam))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 16:52
S36	155	S35 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 16:52
S37	1289	438/4,14.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:51
S38	1157	S37 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:51
S39	837	430/30.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:51
S40	712	S39 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:47

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S41	2	(438/4,14 430/4).ccls. and (semiconductor and critical adj dimension and photoresist and ((e adj beam) (electron adj beam) ebeam)).clm.	US-PGPUB	OR	ON	2006/08/01 14:04
S42	1	@pn="6605951"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 11:47
S43	2	438/14-18.ccor. and functional adj specification	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 11:47
S44	18	438/14-18.ccor. and calculat\$3 near2 operat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:15
S45	15	S44 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 12:01
S46	57	438/14-18.ccor. and calculat\$3 near2 compar\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:07
S47	54	S46 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:32
S48	0	438/14-18.ccor. and second adj device near2 compar\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:08

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S49	0	438/14-18.ccor. and (other third first completed) adj device near2 compar\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:19
S50	1130	438/14.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:15
S51	0	438/14-18.ccor. and (other third first completed) adj device near4 compar\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:19
S52	14	critical adj dimension adj error same compar\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 13:31
S53	14	S52 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 14:16
S54	21	(critical adj dimension and error).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 14:16
S55	18	S54 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 15:17
S56	5	correct\$3 near2 critical adj dimension adj error	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 15:17

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S57	1	S56 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 15:17
S58	192	critical adj dimension same second near5 (device transistor IC circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 09:13
S59	156	S58 and @ad<"20040723"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 09:13